DC-3GHz, 6W, 28V LDMOS Fully matched PA Module

Description

The IMEH0030-6 is a 6-watt ,single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from DC to 3GHz. The module is 50 Ω input/output matched and requires minimal external components.

The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.

Vds=28V, Idq=90mA, CW

Parameter	30MHz	0.5GHz	1.0GHz	1.5GHz	2.0GHz	2.5GHz	3.0GHz	3.3GHz	Units
Linear Gain	20.6	18.1	17.0	15.6	15.6	17.1	15.5	14.9	dB
Pout@Pin=24.5dBm	/	9.7	8.7	7.5	7.6	9.2	6.9	6.0	W
Gain@Pin=24.5dBm	/	15.4	14.9	14.2	14.3	15.1	13.9	13.3	dB
Eff@ Pin=24.5dBm	/	62	44	38	37	46	37	36	%

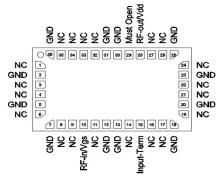
Product Features

- Operating Frequency Range: DC-3GHz
- Operating Drain Voltage: +28 V
- 50 Ω Input/Output
- Psat: ≥6W
- Small signal gain:>14dB, Power gain:>12dB
- Minimum efficiency:>30%
- 6x10 mm Surface Mount Package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC
- Much lower cost than GaN-based ultrawide band PA , due to LDMOS technology used

Applications

- Ultra Broadband Amplifiers
- Fiber Drivers
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

Pin Configuration and Description



Top View

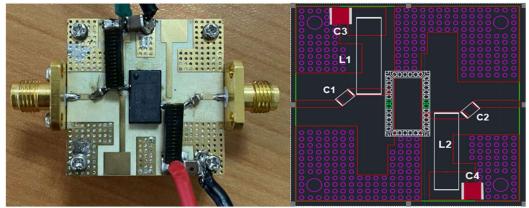


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Pin No.	Symbol			Description		
28	RFout/Vdd	Transistor 1, Drain Bias & RF Output				
10	RFin/Vgs	Transistor 1, RF Input &Gate Bias				
15	Input-Term	Transistor 1, Input 50 ohm term				
29 Must		Keep the pir	Keep the pin open, no GND			
1,3,4,6,8,9,11,14,16,1719,21,22,24,26,27,32-35 NC		No connection				
2,5,7,12,13,16,20,23,25, 30, 31,36 Package GND		DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.				
Table 1. Maximum Ratings						shi damago.
Rating		Symbol		Value		Unit
DrainSource Voltage		V _{DSS}		65		
GateSource Voltage		V _{GS}		-10 to +10		
Operating Voltage		V _{DD}		+32		
Storage Temperature Range		Tstg		-65 to +150		
Case Operating Temperature		Tc	+150			°C
Operating Junction Temperature		TJ	+200			°C
Table 2. Thermal Characteristics			•			•
Characteristic		Symbol	Value			Unit
Thermal Resistance, Junction to Case		D				20.04
T _C = 87°C, T _J =175°C, DC test		Rejc	Rejc 3		°C/W	
Table 3. Electrical Characteristics						
Parameter	Conditio	n	Min	Тур	Max	Unit
Frequency Range			30		3000	MHz
Power Gain @ Psat			12			dB
P _{SAT}		38			dBm	
Drain Efficiency @ P _{SAT}		30			%	
Unless otherwise noted: TA = 25°C, V_{DD} =28 V,	Pulse Width=100	0 us, Duty cycle	=10%			•
Load Mismatch of per Section (On Test Fixture,	50 ohm system	i): V _{DD} = 28 V,	I _{DQ} =90 mA, f =	= 1.6 GHz		
VSWR 10:1 at Psat pulse CW Output Power		No Dev	rice Degradatio	n		

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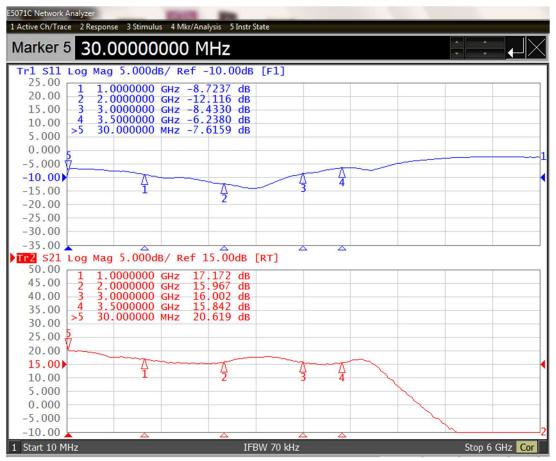
Reference Circuit of Test Fixture Assembly Diagram



		Part NO.	Vendor
C3,C4	10uF 100V chip Capacitor	C5750X7S2A106M230KB	TDK
C1,C2	50V 1uF Chip Capacitor	GRM21BR71H105KA12L	muRata
L1,L2	1.3 uH 4.2A Inductor	4310LC-132KEC	Coilcraft
PCB	RO4350B,20mil,Er=3.48		

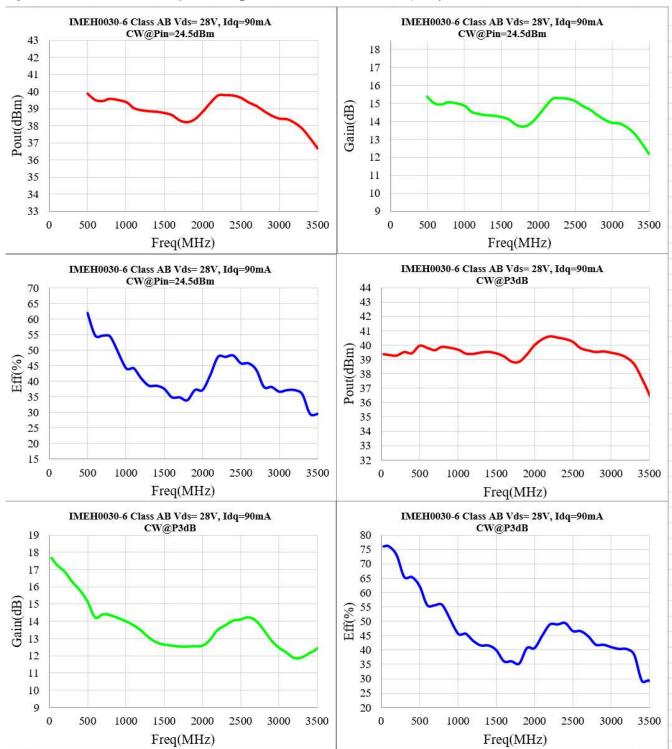
TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm)

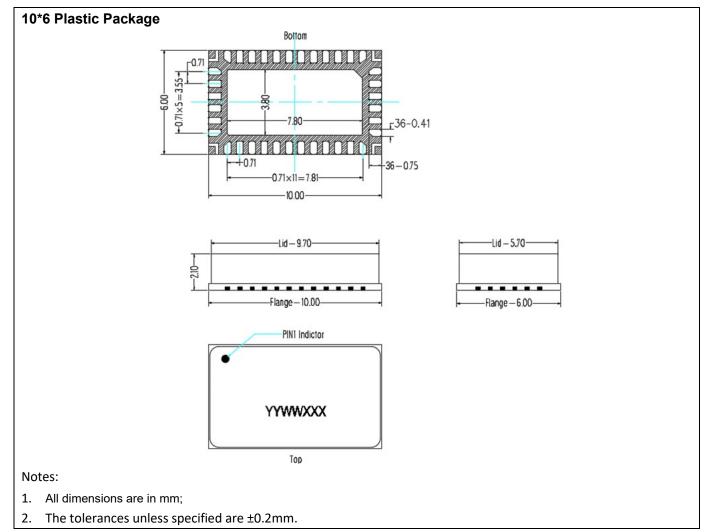


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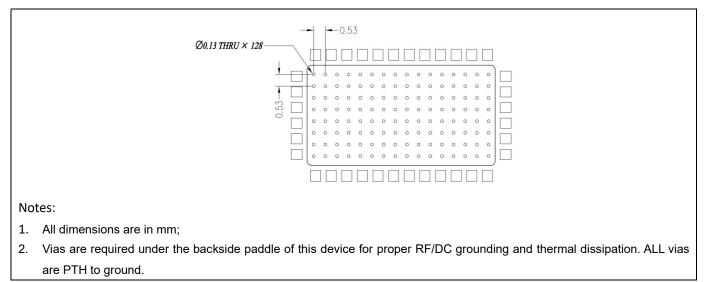
Figure. Power Gain and, efficiency and Pout @Pin=24.5dBm ,and P3dB vs. Frequency



Package Dimensions



Mounting Footprint Pattern



Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2022/12/9	Rev 1.0	Production Datasheet
2023/1/31	Rev 1.1	Modify the pin definition, highlight Pin 29 must be open

Application data based on ZHH-22-04

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